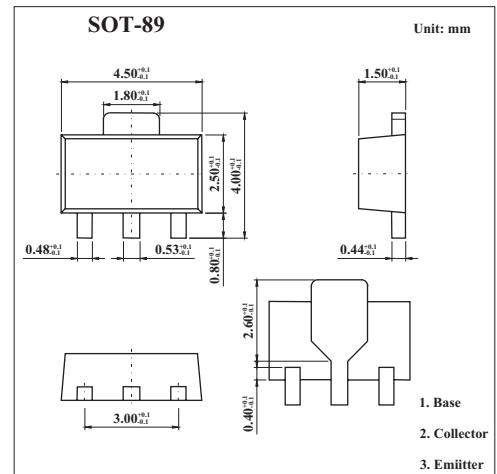


### ■ Features

- 2W power dissipation.
- 12A peak pulse current.
- Excellent HFE characteristics up to 12 amps.
- Extremely low saturation voltage E.g. 8mv Typ.
- Extremely low equivalent on-resistance.
- $R_{CE(sat)}$  50mΩ at 3A.



### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage	$V_{CBO}$	15	V
Collector-emitter voltage	$V_{CEO}$	15	V
Emitter-base voltage	$V_{EBO}$	5	V
Peak pulse current	$I_C$	3	A
Continuous collector current	$I_{CM}$	12	A
Base current	$I_B$	500	mA
Power dissipation	$P_{tot}$	1	W
Operating and storage temperature range	$T_j, T_{stg}$	-55 to +150	°C

## ■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> =100µA	15			V
Collector-emitter breakdown voltage *	V <sub>(BR)CEO</sub>	I <sub>C</sub> =10mA	15			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =100µA	5			V
Collector Cut-Off Current	I <sub>CBO</sub>	V <sub>CB</sub> =10V		0.3	100	nA
Collector Emitter Cut-Off Current	I <sub>CES</sub>	V <sub>CE</sub> =10V		0.3	100	nA
Emitter Cut-Off Current	I <sub>EBO</sub>	V <sub>EB</sub> =4V		0.3	100	nA
Collector-emitter saturation voltage *	V <sub>CE(sat)</sub>	I <sub>C</sub> =0.1A, I <sub>B</sub> =10mA I <sub>C</sub> =1A, I <sub>B</sub> =10mA I <sub>C</sub> =3A, I <sub>B</sub> =50mA I <sub>C</sub> =4A, I <sub>B</sub> =50mA I <sub>C</sub> =5A, I <sub>B</sub> =50mA		8 70 150	14 100 230 300 400	mV
Base-emitter saturation voltage *	V <sub>BE(sat)</sub>	I <sub>C</sub> =3A, I <sub>B</sub> =50mA		0.89	1.0	V
Base-emitter ON voltage *	V <sub>BE(on)</sub>	I <sub>C</sub> =3A, V <sub>CE</sub> =2V		0.82	1.0	V
Static Forward Current Transfer Ratio*	h <sub>FE</sub>	I <sub>C</sub> =10mA, V <sub>CE</sub> =2V I <sub>C</sub> =200mA, V <sub>CE</sub> =2V I <sub>C</sub> =3A, V <sub>CE</sub> =2V I <sub>C</sub> =5A, V <sub>CE</sub> =2V I <sub>C</sub> =12A, V <sub>CE</sub> =2V	200 300 200 150	415 450 320 240 80		
Transitional frequency	f <sub>T</sub>	I <sub>C</sub> =50mA, V <sub>CE</sub> =10V f=50MHz	80	120		MHz
Output capacitance	C <sub>obo</sub>	V <sub>CB</sub> =10V, f=1MHz		30	40	pF
Turn-on time	t <sub>(on)</sub>	I <sub>C</sub> =3A, V <sub>CC</sub> =10V		120		ns
Turn-off time	t <sub>(off)</sub>	I <sub>B1</sub> =I <sub>B2</sub> =50mA		160		ns

\* Pulse test: tp = 300 µs; d ≤ 0.02.

## ■ Marking

Marking	617
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